

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	62	(US-20030068864-\$ or US-20030129827-\$ or US-20040023453-\$ or US-20040069410-\$ or US-20040156987-\$ or US-20040166240-\$).did. or (US-4868617-\$ or US-5252848-\$ or US-5510648-\$ or US-5707896-\$ or US-5753548-\$ or US-5793089-\$ or US-5808347-\$ or US-5817562-\$ or US-5841166-\$ or US-5869875-\$ or US-5886382-\$ or US-5900663-\$ or US-5918137-\$ or US-5942446-\$ or US-5949104-\$ or US-5970352-\$ or US-5989776-\$ or US-6034415-\$ or US-6048772-\$ or US-6051468-\$ or US-6074954-\$ or US-6091110-\$ or US-6100163-\$ or US-6140200-\$ or US-6153905-\$ or US-6180490-\$).did. or (US-6180995-\$ or US-6190978-\$ or US-6214698-\$ or US-6215152-\$ or US-6221727-\$ or US-6222233-\$ or US-6271552-\$ or US-6287931-\$ or US-6291298-\$ or US-6348407-\$ or US-6383913-\$ or US-6399432-\$ or US-6413827-\$ or US-6486061-\$ or US-6495903-\$ or US-6521923-\$ or US-6667219-\$ or US-6674135-\$ or US-6682985-\$ or US-6686627-\$ or US-6689664-\$ or US-6693011-\$ or US-6706640-\$ or US-6716742-\$ or US-6716770-\$ or US-6743695-\$ or US-6756653-\$).did. or (US-6770537-\$ or US-6784486-\$ or US-6794261-\$).did.	US-PGPUB; USPAT	OR	ON	2004/12/09 08:05
L2	108237	(nitrogen near1 gas)	US-PGPUB; USPAT; EPO; JPO	OR	ON	2004/12/09 08:29
L3	2074	L2 and wet and (photoresist (photo near resist))	US-PGPUB; USPAT; EPO; JPO	OR	ON	2004/12/09 08:40
L4	495	L3 and plasma and source and drain and gate	US-PGPUB; USPAT; EPO; JPO	OR	ON	2004/12/09 08:07
L5	341	L4 and substrate and dielectric	US-PGPUB; USPAT; EPO; JPO	OR	ON	2004/12/09 08:07

L6	88	L5 and (metal near1 silicide)	US-PGPUB; USPAT; EPO; JPO	OR	ON	2004/12/09 08:43
L7	4	"6497993"	US-PGPUB; USPAT; EPO; JPO	OR	ON	2004/12/09 08:14
L8	3	("6497993").URPN.	USPAT	OR	ON	2004/12/09 08:20
L9	6	("5460693"   "5612240"   "5880019"   "5922515"   "5932487"   "5942446").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2004/12/09 10:35
L10	22	("5612240").URPN.	USPAT	OR	ON	2004/12/09 08:29
L11	142392	(nitrogen near2 gas)	US-PGPUB; USPAT; EPO; JPO	OR	ON	2004/12/09 10:54
L12	1	11 with substrate with dielectric with (photoresist (photo adj mask)) with plasma with wet	US-PGPUB; USPAT; EPO; JPO	OR	ON	2004/12/09 08:33
L13	5	11 and (substrate with dielectric with (photoresist (photo adj mask)) with plasma with wet)	US-PGPUB; USPAT; EPO; JPO	OR	ON	2004/12/09 08:37
L14	339248	(fabricating forming) with (opening interconnection contact)	US-PGPUB; USPAT; EPO; JPO	OR	ON	2004/12/09 08:39
L15	11442	11 and 14	US-PGPUB; USPAT; EPO; JPO	OR	ON	2004/12/09 08:39
L16	701	15 and (wet near1 (etching etch strip stripping)) and (photoresist (photo near resist) photomask (photo near mask))	US-PGPUB; USPAT; EPO; JPO	OR	ON	2004/12/09 08:42
L17	511	16 and (dielectric insulation)	US-PGPUB; USPAT; EPO; JPO	OR	ON	2004/12/09 08:43
L18	104	17 and (metal near1 silicide)	US-PGPUB; USPAT; EPO; JPO	OR	ON	2004/12/09 08:43
L19	90	18 and gate	US-PGPUB; USPAT; EPO; JPO	OR	ON	2004/12/09 15:18
L20	52	19 not 6	US-PGPUB; USPAT; EPO; JPO	OR	ON	2004/12/09 14:48
L21	25	20 and (planarization planarizing polishing)	US-PGPUB; USPAT; EPO; JPO	OR	ON	2004/12/09 08:51
L22	27	20 not 21	US-PGPUB; USPAT; EPO; JPO	OR	ON	2004/12/09 08:51

L23	106	("5286344").URPN.	USPAT	OR	ON	2004/12/09 09:12
L24	21	19 and (wet with remov\$3 with (photoresist mask))	US-PGPUB; USPAT; EPO; JPO	OR	ON	2004/12/09 10:29
L25	37940	(method process) with (forming fabricating) with opening	US-PGPUB; USPAT; USOCR; EPO; JPO	OR	ON	2004/12/09 10:51
L26	14459	(providing forming) with ((dielectric insulation) near1 layer) with substrate	US-PGPUB; USPAT; USOCR; EPO; JPO	OR	ON	2004/12/09 10:40
L27	1203	(patterned patterning) with (photoresist near1 layer) with ((dielectric insulation) near1 layer)	US-PGPUB; USPAT; USOCR; EPO; JPO	OR	ON	2004/12/09 10:52
L28	16306	etching with ((dielectric insulation) near1 layer)	US-PGPUB; USPAT; USOCR; EPO; JPO	OR	ON	2004/12/09 10:56
L29	355	plasma with (photoresist near1 layer) with gas	US-PGPUB; USPAT; USOCR; EPO; JPO	OR	ON	2004/12/09 10:53
L30	2995	wet with (remove removed removing) with photoresist	US-PGPUB; USPAT; USOCR; EPO; JPO	OR	ON	2004/12/09 10:43
L31	3	25 and 26 and 27 and 28 and 29 and 30	US-PGPUB; USPAT; USOCR; EPO; JPO	OR	ON	2004/12/09 10:43
L32	131033	(method process) with (forming fabricating) with (opening hole vias contact interconnection)	US-PGPUB; USPAT; USOCR; EPO; JPO	OR	ON	2004/12/09 10:51
L33	1655	(patterned patterning forming providing) with (photoresist near1 layer) with ((dielectric insulation) near1 layer)	US-PGPUB; USPAT; USOCR; EPO; JPO	OR	ON	2004/12/09 10:52
L34	2661	plasma with (photoresist near1 layer)	US-PGPUB; USPAT; USOCR; EPO; JPO	OR	ON	2004/12/09 10:53
L35	160242	(nitrogen near3 gas)	US-PGPUB; USPAT; EPO; JPO	OR	ON	2004/12/09 10:55

L36	16635	(etching stripping) with ((dielectric insulation) near1 layer)	US-PGPUB; USPAT; USOCR; EPO; JPO	OR	ON	2004/12/09 10:57
L37	7	32 and 33 and 34 and 35 and 30 and 36	US-PGPUB; USPAT; EPO; JPO	OR	ON	2004/12/09 10:57
L38	0	10/667013	US-PGPUB; USPAT; EPO; JPO	OR	ON	2004/12/09 13:43
L39	0	"10667013"	US-PGPUB; USPAT; EPO; JPO	OR	ON	2004/12/09 13:43
L40	31	TSAI-MING-HU TSAI-MING-HUAN TSAI-MING-HUANG TSAI-MING-HUNG	US-PGPUB; USPAT; EPO; JPO	OR	ON	2004/12/09 15:18